

**METHOD FOR POLYSILICON CONDUCTOR (PC) TRIMMING FOR
SHRINKING CRITICAL DIMENSION AND ISOLATED-NESTED
OFFSET CORRECTION**

ABSTRACT

5 A method of forming a semiconductor device, includes providing a
structure having a first critical dimension, forming a lithographic pattern on the
structure, and etching the structure with an O₂-containing material to trim the first
critical dimension to a second critical dimension, the second critical dimension
being smaller than the first critical dimension. Thereafter, any offset between the
10 nested features and the isolated feature can be corrected.